

IGBT Discrete

$\mathbf{V}_{\mathbf{CE}}$	650	V
I_{C}	20	A
V _{CE(SAT)} I _C =20A	1.6	V

Applications

- · Inverter for motor drive
- · AC and DC servo drive amplifier
- · Uninterruptible power supply

Features

- High breakdown voltage to 650V for improved reliability
- . Maximum junction temperature 175℃
- · Positive temperature coefficient
- . Including fast & soft recovery anti-parallel FWD
- High short circuit capability(10us)

Maximum Ratings ($T_j = 25$ °C unless otherwise specified):

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	$ m V_{CE}$	650	V
DC Collector Current, limited by T_{jmax} $T_C=25^{\circ}C$ $T_C=100^{\circ}C$	I_{C}	40 20	A
Diode Forward Current, limited by T_{jmax} T_{C} = 25°C T_{C} = 100°C	${ m I_F}$	40 20	A
Continuous Gate-Emitter Voltage	$ m V_{GE}$	±20	V
Transient Gate-Emitter Voltage (tp≤10μs,D<0.010)	V_{GE}	±30	V
Pulsed Collector Current, V_{GE} =15V, tp limited by T_{jmax}	Ісм	60	A
Diode Pulsed Current, tp limited by T _{jmax}	I_{Fpuls}	60	A
Power Dissipation ,Tc=25°C	P_{tot}	145	W
Power Dissipation , Tc=100°C	P _{tot}	61	W

Rev.1.0



Operating Junction Temperature	$T_{\rm j}$	-40+175	°C
Storage Temperature	$T_{\rm s}$	-55+150	°C
Soldering Temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	°C

Electrical Characteristics of the IGBT $(T_j=25^{\circ}Cunless otherwise specified)$:

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Static						
Collector-Emitter Breakdown Voltage	BV _{CES}	V _{GE} =0V, I _C =250μA	650	-	-	V
Gate Threshold Voltage	$V_{\text{GE(th)}}$	$V_{GE}=V_{CE}, I_{C}=1 \text{ mA}$	4	5.5	6.8	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} =15V, I _C =20A T _j =25°C, T _j =125°C T _i =150°C	-	1.6 1.8 2.1	2.2	V
Zero Gate Voltage Collector Current	I _{CES}	V _{CE} =650V, V _{GE} =0V T _j = 25°C, T _j =150°C	-	-	1.00 4.00	mA
Gate-Emitter Leakage Current	I _{GES}	V_{CE} = 0V, V_{GE} = ± 20V	-	-	±200	nA

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Dynamic						
Input Capacitance	Cies		-	1680	-	
Onput Capacitance	Coes	V_{CE} = 30V, V_{GE} = 0V, f = 1MHz	-	66	-	pF
Reverse Transfer Capacitance	C _{res}		-	43	-	
Gate Charge	Q_{g}		-	101	-	
Gate-Emitter Charge	Q_{ge}	$V_{CC}=300V,I_{C}=20A, V_{GE}=15V$	-	22	-	nC
Gate-Collector Charge	$Q_{ m gc}$		-	52	-	



Switching Characteristic, Inductive Load (T_j= 25°C unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-on Delay Time	t _{d(on)}		-	32	-	ns
Rise Time	$t_{\rm r}$		-	38	-	ns
Turn-on Energy	Eon	$V_{CC} = 300V, I_{C} = 20A,$	-	0.66	-	mJ
Turn-off Delay Time	$t_{d(off)}$	V_{GE} = -15V~15V, R _g =10 Ω	-	150	-	ns
Fall Time	$t_{ m f}$		-	30	-	ns
Turn-off Energy	E _{off}		-	0.5	-	mJ

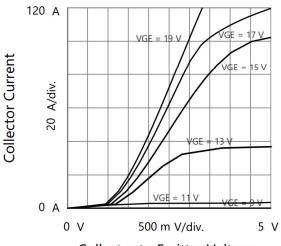
Electrical Characteristics of the DIODE $(T_j=25^{\circ}Cunless otherwise specified)$:

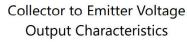
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Diode Forward Voltage	V_{F}	$I_F = 10A$	-	1.4	2.1	V
Reverse Recovery Current	I_{rr}		-	4	-	A
Reverse Recovery Charge	Qrr	$I_F=10A, V_R=300V,$ $di/dt=-200A/\mu s,$	-	201	-	nC
Reverse Recovery Energy	Erec		-	0.15	-	mJ

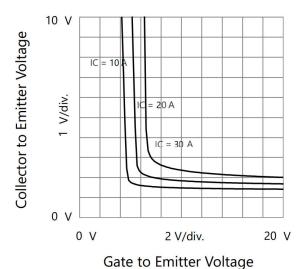
Thermal Resistance

Parameter	Symbol	Max. Value	Unit
IGBT Thermal Resistance, Junction - Case	R _{th} (j-c)	0.88	°C/W
Diode Thermal Resistance, Junction - Case	R _{th} (j-c)	2.79	°C/W
Thermal Resistance, Junction - Ambient	R _{th} (j-a)	59	°C/W

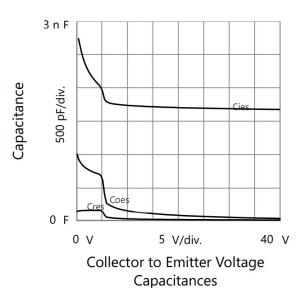


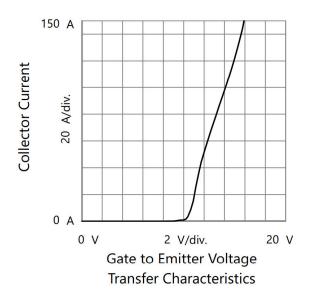


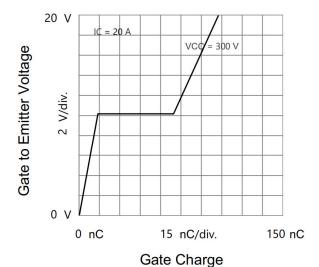




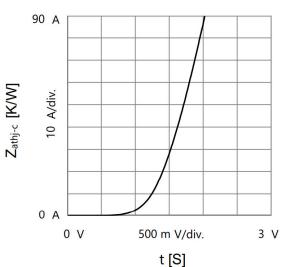
Collector to Emitter Voltage vs. Gate to Emitter Voltage





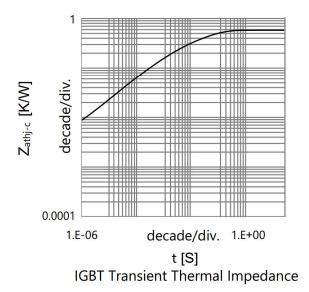


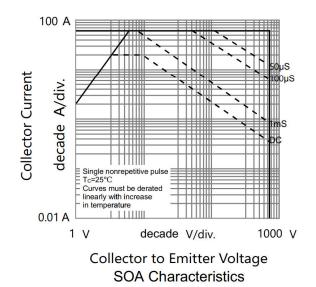
Gate to Emitter Voltage vs. Gate Charge



IGBT Transient Thermal Impedance

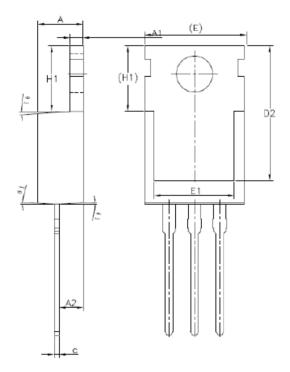


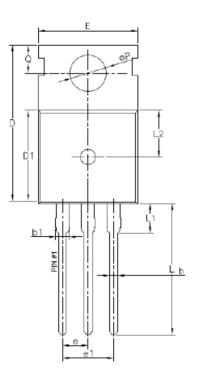




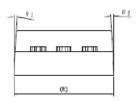


TO-220 Package Outline Information





SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	1.27	1.30	1.33
A2	2.30	2.40	2.50
b	0.70	-	0.90
b1	1.27	-	1.40
С	0.45	0.50	0.60
D	15.30	15.70	16.10
D1	9.10	9.20	9.30
D2	13.10	_	13.70
E	9.70	9.90	10.20
E1	7.80	8.00	8.20
e	2.49	2.54	2.59
e1	5.03	5.08	5.12
H1	6.30	6.50	6.70
L	12.78	13.08	13.38
L1	3.30	_	3.50
L2	4.50	4.60	4.70
ØΡ	3.55	3.60	3.65
Q	2.73	-	2.87
θ1	1"	3°	5'



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